

Absolute Maximum Ratings

V _{BAT}	–0.5V to 25V
VER	–0.5V to 25V
V _{OUT}	–0.5V to 7V
Digital Input/ Output Voltage	–0.5V to 7V
Peak Transient Voltage (36V Load Dump @ 14V battery voltage)	50V
Storage Temperature Range	–55° to 150°C
Junction to Free Air Thermal Impedance	55°C/W
ESD Susceptibility (Human Body Model)	4kV
Lead Temperature Soldering: Reflow (SMD styles only)	60 sec. max above 183°C, 230°C peak
T _A	–40°C to 85°C
T _J	–40°C to 150°C

**Electrical Characteristics: $8V \leq V_{BAT} \leq 16V$, $8V \leq VER \leq 25V$, $1mA \leq I_{V(OUT)} \leq 100mA$,
T_{TEST} = –40°C to 125°C, unless otherwise specified.**

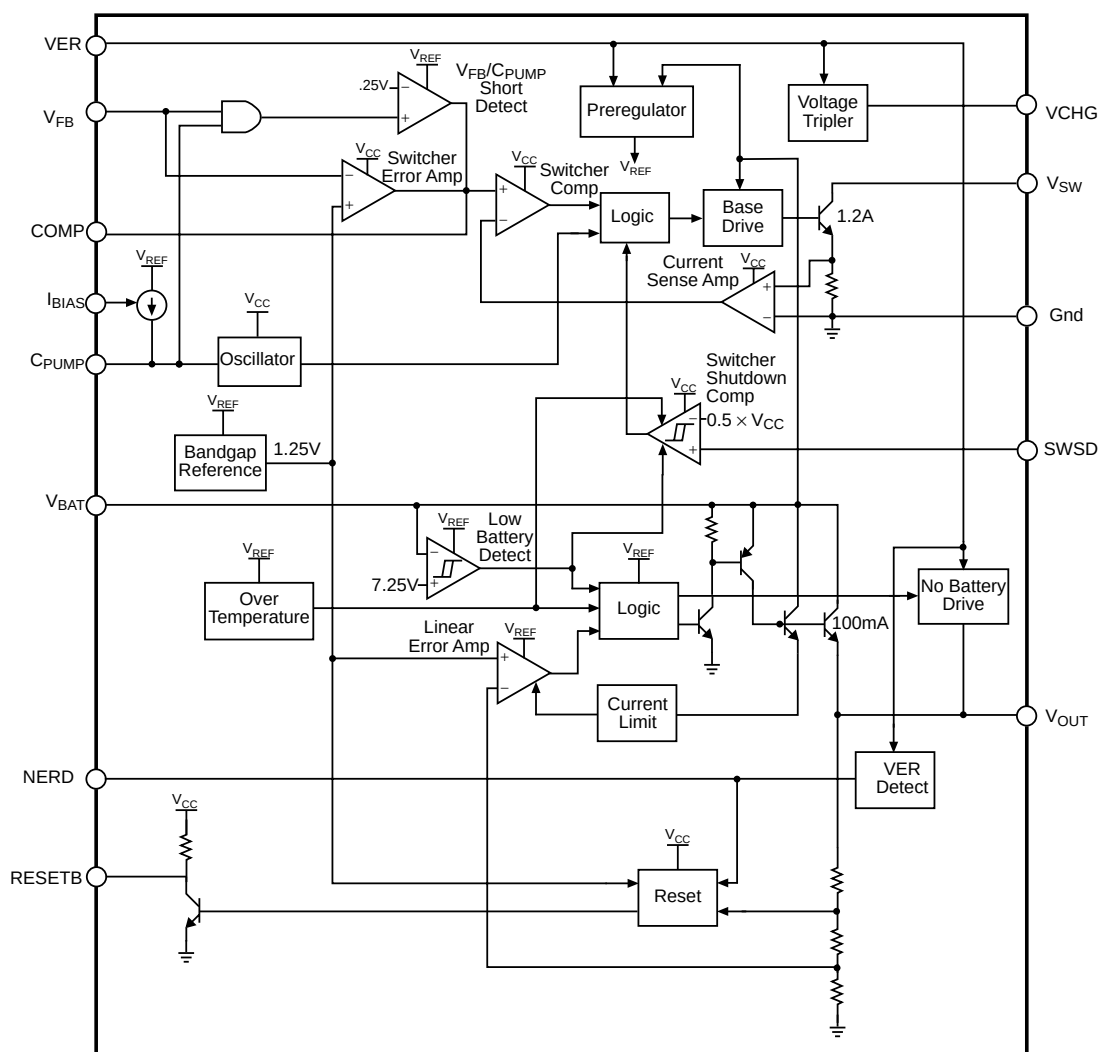
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
■ Linear Regulator					
Output Voltage	Output driven from V _{BAT} : VER = 25V Output driven from VER: V _{BAT} = 0V	4.9 4.9		5.1 5.1	V V
Regulator Bias Current (from V _{BAT})	I _{V(BAT)} @ I _{V(OUT)} = –100mA, SWSD = 4V, V _{BAT} = 16V, VER = 25V T = –40°C T = 25°C T = 125°C			8 7 6	mA mA mA
Regulator Bias Current (from VER)	I _{VER} @ I _{V(OUT)} = –100mA SWSD = 4V, V _{BAT} = 0V, VER = 25V T = –40°C T = 25°C T = 125°C			11 9 8	mA mA mA
Dropout Voltage V _{BAT} – V _{OUT}	VER = 25V, I _{V(OUT)} = –100mA (probe only)			1.5	V
Dropout Voltage VER – V _{OUT}	V _{BAT} = 0V, I _{V(OUT)} = –100mA			1.5	V
Smart Switch Threshold V _{BAT} to VER	VER = 25V, I _{V(OUT)} = –50mA	6.5		8.0	V
Smart Switch Threshold Hysteresis	VER = 25V, I _{V(OUT)} = –50mA	0.5		1.0	V
V _{OUT} Output Noise	V _{BAT} = 16V, VER = 25V, I _{V(OUT)} = –1mA C = 10μF, ESR = 0.5Ω			0.050	V
Line Regulation				0.025	V
Load Regulation				0.025	V
Output Current Limit		120			mA
■ Switching Regulator					
	VER = 25V, I_{V(OUT)} = –1mA				
Switching Frequency	C _{PUMP} = 270pF, R _{I(BIAS)} = 30.1kΩ	135	150	165	kHz
Pump Drive Current	ΔI _{V(BAT)} for 0A ≤ I _{V(SW)} ≤ 1.2A			50	mA
Switch Saturation Voltage	I _{V(SW)} = 1.2A			1.6	V
Output Current Limit		1.2		2.4	A
V _{FB} Regulation		1.238	1.270	1.303	V
V _{FB} Input Current	V _{FB} above short low detection level			1	μA
V _{FB} Input Shorted Low Detection Level		200	250	300	mV

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 $T_{TEST} = -40^{\circ}C$ to $125^{\circ}C$, unless otherwise specified.**

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
■ Switching Regulator: continued					
C_{PUMP} Short detection threshold		200	250	300	mV
Maximum Duty Cycle		80		95	%
V_{SW} Leakage Current	$I_{V(SW)} @ V_{SW} = 50V$, $SWSD = V_{OUT}$			100	μA
■ Voltage Tripler $V_{BAT} = 16V$, $I_{V(OUT)} = -1mA$, $C_{CHG} = 1.5\mu F$					
Output Voltage Clamp $V_{CHG} - VER$	$VER = 8V$, $I_{V(CHG)} = -30\mu A$ $VER = 12V$, $I_{V(CHG)} = -90\mu A$	6.25 6.25	8.00 8.00	13.00 13.00	V V
Initial Charge Time	$C_{CHG} = 0.15\mu F$, $VER = 8V$, $V_{CHG} = 14.25V$			30	ms
Maximum Output Voltage Clamp V_{CHG}		25	32.5	40	V
Output Voltage Clamp V_{CHG}	$VER = 28V$, $I_{V(CHG)} = 0\mu A$	25	32.5	40	V
Short Circuit Path Current Limit VER to V_{CHG}				3	mA
■ RESETB OUTPUT $V_{BAT} = 0V$					
High Threshold	V_{OUT} increasing	4.525	4.750	4.850	V
Low Threshold	V_{OUT} decreasing	4.500	4.650	4.825	V
Hysteresis		25	100	200	mV
Output Low Voltage	$V_{OUT} = 1.0V$, $I_{RESETB} = 100\mu A$ $I_{RESETB} = 1mA$, $V_{OUT} = 4.5V$			0.5 0.5	V V
Pull-Up Resistor	$RESETB = 1V$	25	50	100	k Ω
■ SWSD INPUT $V_{BAT} = 16V$, $VER = 25V$, $I_{V(OUT)} = -1mA$					
High Threshold				$0.7 \times V_{OUT}$	V
Low Threshold		$0.3 \times V_{OUT}$			V
Input Impedance	referenced to ground	10	20	40	k Ω
■ NERD OUTPUT $V_{BAT} = 16V$, $I_{V(OUT)} = -1mA$, $C_{NERD} = 0.47\mu F$					
VER Detection Voltage		1.5		6.5	V
Output Low Voltage	$I_{NERD} = 1mA$, $V_{OUT} = 4.5V$			0.5	V
Pull-Up Current	$NERD = 0.5V$	30	40	50	μA
Power on Delay		6.25	8.5	11	ms
Clamping Voltage (low)	VER present	1.00	1.25	1.50	V
Clamping Voltage (high)	VER not present	3.50	3.75	4.00	V
■ GENERAL					
VER Load Current	$VER = 25V$, $V_{BAT} = 16V$, $I_{V(OUT)} = -100mA$ $T = -40^{\circ}C$ $T = 25^{\circ}C$ $T = 125^{\circ}C$			5 5 4	mA mA mA
Thermal Shutdown	(guaranteed by design)	160		210	$^{\circ}C$

Package Pin Description

PACKAGE PIN #	PIN SYMBOL	FUNCTION
20 Lead SO Wide <i>(internally fused leads)</i>		
1	VER	Energy reserve input.
2	V _{BAT}	Battery input.
3	V _{FB}	Charge PUMP control voltage input.
4	Gnd1	Ground.
5	Gnd2	Ground.
6	Gnd3	Ground.
7	Gnd4	Ground.
8	V _{SW}	Charge PUMP switch collector.
9	SWSD	Charge PUMP shutdown input.
10	COMP	Charge PUMP compensation pin.
11	C _{PUMP}	Charge PUMP timing cap input.
12	I _{BIAS}	Reference current resistor pin.
13	V _{CHG}	Switched cap voltage tripler output.
14	Gnd5	Ground.
15	Gnd6	Ground.
16	Gnd7	Ground.
17	Gnd8	Ground.
18	NERD	No energy reserve detected output.
19	RESETB	Reset output.
20	V _{OUT}	Linear regulator output.



Circuit Description

Figure 1 is an oscilloscope waveform showing the charge pump collector voltage, collector current and the charge pump timing capacitor during normal operation with $I_{VER} = 30\text{mA}$.

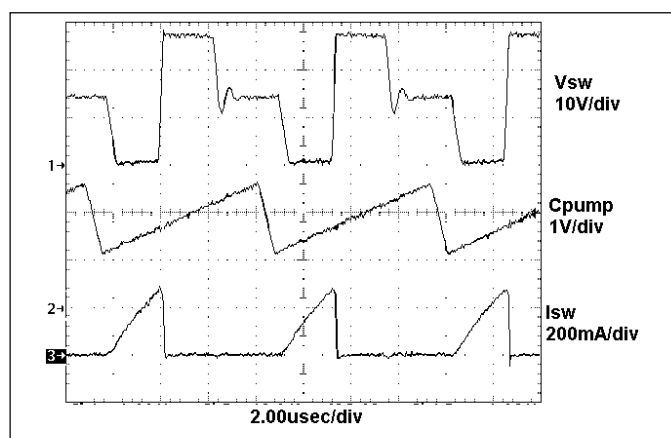


Figure 1. Typical operation with $I_{VER} = 30\text{mA}$.

Figure 2 is an oscilloscope waveform showing the voltage tripler output and the energy reserve input during power up.

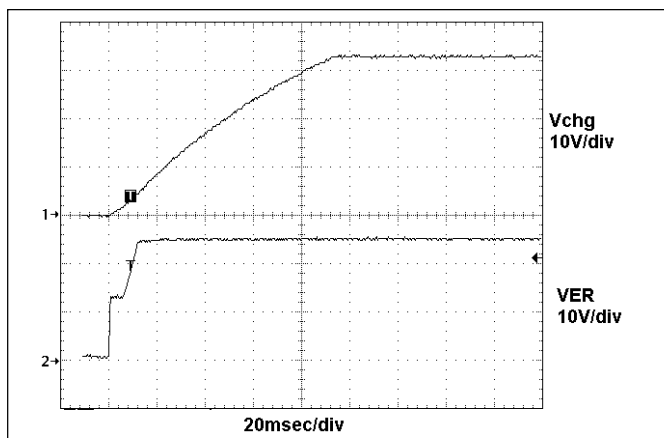


Figure 2. Startup with $R_{V(CHG)} = 510\text{k}$.

Package Specification

PACKAGE DIMENSIONS IN mm (INCHES)

Lead Count	D			
	Metric		English	
	Max	Min	Max	Min
24 Lead SO Wide	13.00	12.60	.512	.496

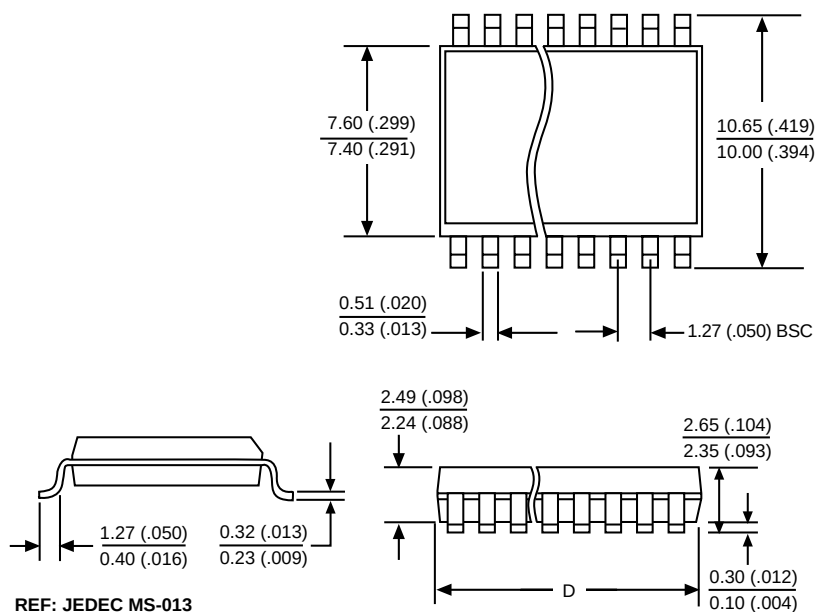
PACKAGE THERMAL DATA

Thermal Data

20 Lead SO Wide (internally fused leads)

R _{ΘJC}	typ	9	°C / W
R _{ΘJA}	typ	55	°C / W

Surface Mount Wide Body (DW); 300 mil wide



Ordering Information

Part Number	Description
CS2001YDWF20	20 Lead SO Wide (internally fused leads)
CS2001YDWFR20	20Lead SO Wide (internally fused leads) (tape & reel)

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